

## GM194A

### NPN SILICON PLANAR MEDIUM POWER TRANSISTOR

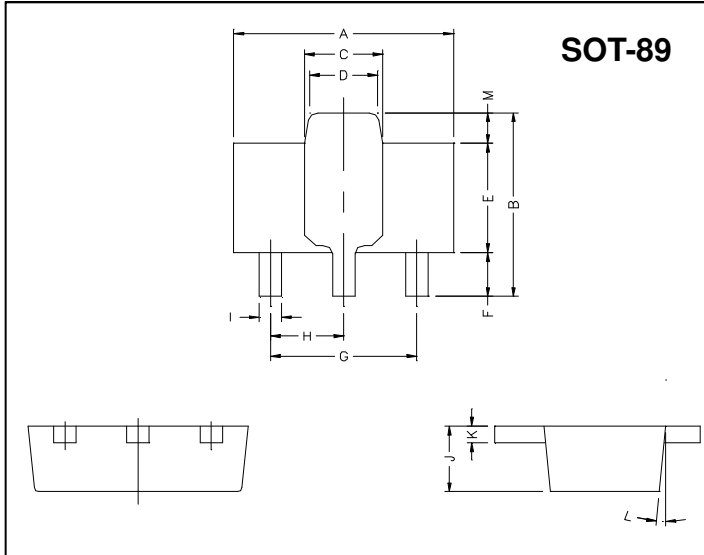
#### Description

The GM194A is designed for medium power amplifier applications.

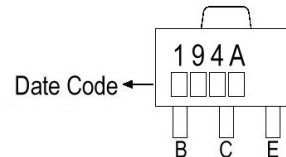
#### Features

- 1 Amp continuous current
- Complementary to GM195A

#### Package Dimensions



#### Marking :



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.4	4.6	G	3.00	REF.
B	4.05	4.25	H	1.50	REF.
C	1.50	1.70	I	0.40	0.52
D	1.30	1.50	J	1.40	1.60
E	2.40	2.60	K	0.35	0.41
F	0.89	1.20	L	5° TYP.	
			M	0.70 REF.	

#### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	°C
Storage Temperature	Tstg	-65~+150	°C
Collector to Base Voltage	Vcbo	40	V
Collector to Emitter Voltage	Vceo	40	V
Emitter to Base Voltage	Vebo	5	V
Collector Current (DC)	Ic	1	A
Collector Current (Pulse)	Ic	2	A
Total Power Dissipation	Pd	1	W

#### Electrical Characteristics (Ta = 25°C, unless otherwise stated)

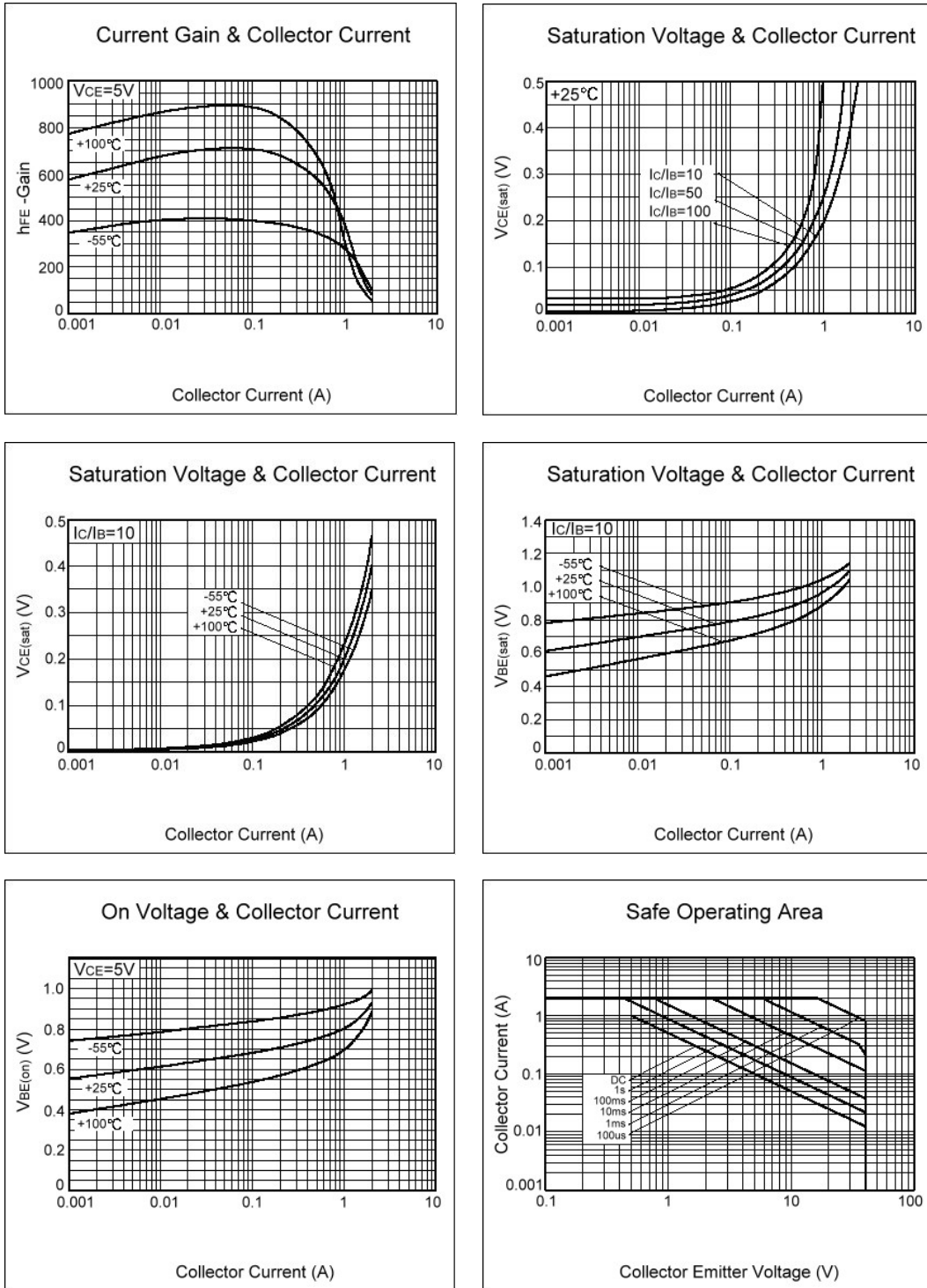
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Vcbo	40	-	-	V	Ic=100uA, Ie=0
*Vceo	40	-	-	V	Ic=10mA, Ib=0
Vebo	5	-	-	V	Ie=100uA, Ic=0
Icbo	-	-	100	nA	Vcb=30V, Ie=0
Ices	-	-	100	nA	Vces=30V
Iebo	-	-	100	nA	VEB=4V, Ic=0
*Vce(sat)1	-	-	0.3	V	Ic=500mA, Ib=50mA
*Vce(sat)2	-	-	0.5	V	Ic=1A, Ib=100mA
*Vbe(sat)	-	-	1.1	V	Ic=1A, Ib=100mA
*Vbe(on)	-	-	1.0	V	Vce=5V, Ic=1A
*hfe1	300	-	-		Vce=5V, Ic=1mA
*hfe2	300	-	900		Vce=5V, Ic=500mA
*hfe3	200	-	-		Vce=5V, Ic=1A
*hfe4	35	-	-		Vce=5V, Ic=2A
fT	150	-	-	MHz	Vce=10V, Ic=50mA, f=100MHz
Cob	-	-	10	pF	Vcb=10V, Ie=0, f=1MHz

\*Measured under pulse condition. Pulse width=300μs, Duty Cycle≤2%

#### Classification Of hFE2

Rank	P	Q
Range	300 ~ 700	500 ~ 900

## Characteristics Curve



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